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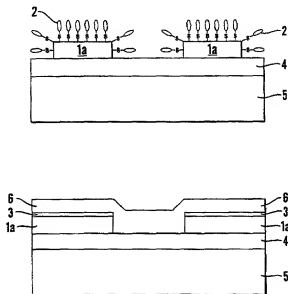
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(54) Title: A MEANS FOR ELECTRICAL CONTACTING OR ISOLATION OF ORGANIC OR INORGANIC SEMICONDUCTORS AND A METHOD FOR ITS FABRICATION



(57) Abstract: In a means for electrical contacting or isolation of organic or inorganic semiconductors in electronic and optoelectronic devices, particularly thin-film devices, the means comprises a substrate (1) in the form of a contact material (1a) or an isolating material (4). A charge transfer material (2) is provided patterned or unpatterned on or at the surface of the substrate and includes charge transfer components in the form of donors and/or acceptors. The charge transfer material forms a self-assembling layer (3) on one or more atomic and/or molecular layers. The charge transfer material (2) has a direct or indirect bond to the surface of the substrate (1) and further forms a charge transfer complex with a thereabove adjacently provided organic or inorganic semiconductor (6). The charge transfer material (2) then forms a donor or acceptor material in the charge transfer complex depending upon respectively whether the semiconductor (6) itself is an acceptor or donor material.

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